

IN THE CLAIMS:

1.-34. (Cancelled)

35. (Currently Amended) A semiconductor light emitting device comprising:

a base substrate;

~~a multilayer epitaxial structure includes a first conductive layer, a second
conductive layer and a light emitting layer that is formed between the first conductive layer and
the second conductive layer, the multilayer epitaxial structure being formed on the base substrate
in such a manner that the first conductive layer is positioned closer to the base substrate than the
second conductive layer is;~~

~~a first electrode that is formed on the first conductive layer;~~

~~a second electrode that is formed on the second conductive layer;~~

~~an insulating film that covers side surfaces of the multilayer epitaxial structure
and separates the first electrode and the second electrode;~~

~~a first power supply terminal and a second power supply terminal that are formed
on a main surface of the base substrate which faces away from the multilayer epitaxial structure;~~

~~a first conductive member including a first through hole that is provided in the
base substrate, and electrically connecting the first electrode and the first power supply terminal;~~

~~a second conductive member including a second through hole that is provided in
the base substrate, and electrically connecting the second electrode and the second power supply
terminal; and~~

~~a phosphor film having an even thickness that covers a main surface of the
multilayer epitaxial structure.~~

a base substrate (4); and

a pair of power supply terminal thin-film layers (36, 38), each being provided on different areas of a first main surface of the base substrate, and the pair of power supply terminal thin-film layers being electrically connected to each other via through-holes (42, 46) provided in the base substrate, wherein

a second main surface of the base substrate has provided thereon a semiconductor multilayer epitaxial structure including a first conductive layer (16), a light emitting layer (14), and a second conductive layer (12) formed in the stated order,

a first electrode thin-film layer (22) is in contact with the first conductive layer,

a second electrode thin-film layer (24) is in contact with the second conductive layer,

a phosphor film covers the semiconductor multilayer epitaxial structure, and

a first thin-film layer (40) and a second thin-film layer (30) electrically connect the first electrode thin-film layer (22) and the second electrode thin-film layer (24) respectively via the through-holes.

36. (Previously Presented) The semiconductor light emitting device of Claim 35, wherein

the multilayer epitaxial structure is formed on the base substrate leaving a space along each edge of a main surface of the base substrate which faces the multilayer epitaxial structure; and

the first through hole and the second through hole are provided in a peripheral portion of the base substrate, the peripheral portion corresponding to the space.

37. (Previously Presented) The semiconductor light emitting device of Claim 35, further comprising:

a metal reflective film that is sandwiched between the multilayer epitaxial structure and the base substrate.

38.-39. (Cancelled)

40. (Previously Presented) The semiconductor light emitting device of Claim 35 wherein

the multilayer epitaxial structure having a structural characteristic of epitaxial growth on a single-crystal substrate different from the base substrate, is mounted on the base
5 substrate.

41. (Currently Amended) The semiconductor light emitting device of Claim 40, wherein

the multilayer epitaxial structure is mounted to the base substrate in such a manner that a last epitaxially-grown layer having grown on ~~[[a]]~~ the single-crystal substrate
5 different from the base substrate is positioned closer to the base substrate than a first epitaxially-grown layer is.

42.-45. (Cancelled)

46. (Previously Presented) The semiconductor light emitting device of Claim 35, wherein

the first and the second through holes are positioned in a periphery of the base substrate, and

5 the multilayer epitaxial structure is not positioned on or over the first and second through holes.

47. (Cancelled)

48. (Currently Amended) The semiconductor light emitting device of Claim [[47]]
35, wherein

the multilayer epitaxial structure is mounted on the base substrate in such a manner that a last epitaxially-grown layer having a structure characteristic of being grown on a
5 single-crystal substrate different from the base substrate is positioned closer to the base substrate than a portion of a first epitaxially-grown layer.

49. (Currently Amended) The semiconductor light emitting device of Claim [[47]] 48 wherein the base substrate is a SiC substrate.

50.-51. (Cancelled)

52. (New) The semiconductor light emitting device of Claim 35, wherein
the phosphor layer covers an entirety of the base substrate, including surrounding
edge portions of the base substrate, and

a peripheral lateral surface of the base substrate and a peripheral lateral surface of
5 the phosphor layer are a continuous surface.